

isc Silicon NPN Pow Transistor

2SC2482

DESCRIPTION

- High breakdown voltage
- Low output capacitance
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

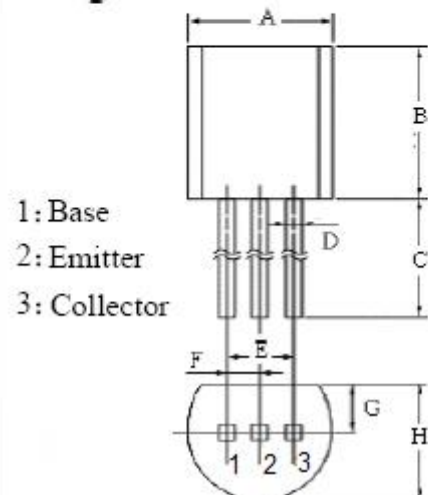
APPLICATIONS

- Color TV chroma output applications
- Color TV horiz. driver applications
- High voltage switching and amplifier applications

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	300	V
V_{CEO}	Collector-Emitter Voltage	300	V
V_{EBO}	Emitter-Base Voltage	7	V
I_C	Collector Current-Continuous	0.1	A
P_C	Collector Power Dissipation @ $T_c=25^\circ\text{C}$	0.9	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$

TO-92 package



DIM	mm	
	MIN	MAX
A	4.33	4.83
B	4.33	4.83
C	14.0	15.0
D	0.36	0.56
E	2.54	
F	1.27	
G	0.92	1.12
H	3.40	3.60

isc Silicon NPN Pow Transistor**2SC2482****ELECTRICAL CHARACTERISTICS****T_c=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 10mA ; I _B = 1mA			1.0	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	I _C =10mA ; I _B = 1mA			1.0	V
I _{CB0}	Collector Cutoff Current	V _{CB} = 240V; I _E = 0			1	μ A
h _{FE}	DC Current Gain	I _C = 20mA ; V _{CE} = 10V	30		150	
f _T	Current-Gain—Bandwidth Product	I _C = 20mA ; V _{CE} = 10V		50		MHz